

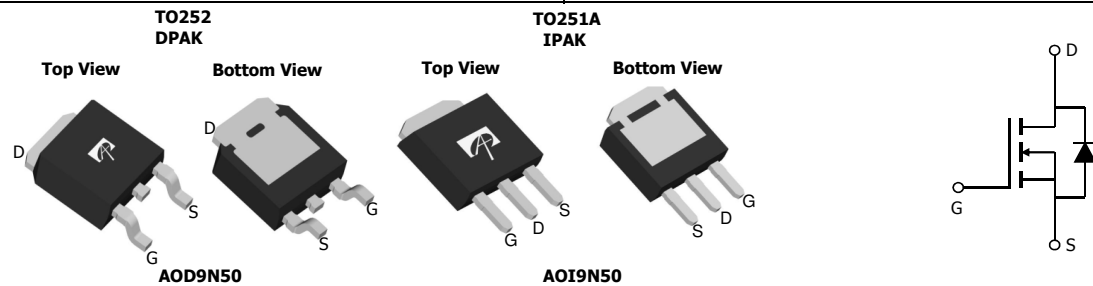
General Description

The AOD9N50 & AOI9N50 have been fabricated using an advanced high voltage MOSFET process that is designed to deliver high levels of performance and robustness in popular AC-DC applications. By providing low $R_{DS(on)}$, C_{iss} and C_{rss} along with guaranteed avalanche capability these parts can be adopted quickly into new and existing offline power supply designs.

Product Summary

V_{DS}	600V@150°C
I_D (at $V_{GS}=10V$)	9A
$R_{DS(on)}$ (at $V_{GS}=10V$)	< 0.86Ω

100% UIS Tested!
100% R_g Tested!



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	500	V
Gate-Source Voltage	V_{GS}	± 30	V
Continuous Drain Current ^B	I_D	9	A
		5.7	
Pulsed Drain Current ^C	I_{DM}	27	
Avalanche Current ^C	I_{AR}	3.8	A
Repetitive avalanche energy ^C	E_{AR}	216	mJ
Single pulsed avalanche energy ^H	E_{AS}	433	mJ
Peak diode recovery dv/dt	dv/dt	5	V/ns
Power Dissipation ^B	P_D	178	W
		1.4	W/°C
Junction and Storage Temperature Range	T_J, T_{STG}	-50 to 150	°C
Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds	T_L	300	°C

Thermal Characteristics

Parameter	Symbol	Typical	Maximum	Units
Maximum Junction-to-Ambient ^{A,G}	$R_{\theta JA}$	45	55	°C/W
Maximum Case-to-sink ^A	$R_{\theta CS}$	-	0.5	°C/W
Maximum Junction-to-Case ^{D,F}	$R_{\theta JC}$	0.5	0.7	°C/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V, T _J =25°C	500			V
		I _D =250μA, V _{GS} =0V, T _J =150°C		600		
BV _{DSS} /ΔT _J	Zero Gate Voltage Drain Current	I _D =250μA, V _{GS} =0V		0.56		V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =500V, V _{GS} =0V			1	μA
		V _{DS} =400V, T _J =125°C			10	
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±30V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =5V, I _D =250μA	3.3	3.9	4.5	V
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =4.5A		0.71	0.86	Ω
g _{FS}	Forward Transconductance	V _{DS} =40V, I _D =4.5A		9		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.72	1	V
I _S	Maximum Body-Diode Continuous Current				9	A
I _{SM}	Maximum Body-Diode Pulsed Current				27	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =25V, f=1MHz	760	962	1160	pF
C _{oss}	Output Capacitance		65	98	130	pF
C _{rss}	Reverse Transfer Capacitance		4.5	8	12	pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz	1.5	3.2	5	Ω
SWITCHING PARAMETERS						
Q _g	Total Gate Charge	V _{GS} =10V, V _{DS} =400V, I _D =9A	15	19.5	24	nC
Q _{gs}	Gate Source Charge			4.6		nC
Q _{gd}	Gate Drain Charge			7.1		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =250V, I _D =9A, R _G =25Ω		24		ns
t _r	Turn-On Rise Time			44		ns
t _{D(off)}	Turn-Off DelayTime			55		ns
t _f	Turn-Off Fall Time			35		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =9A, dI/dt=100A/μs, V _{DS} =100V	260	332	400	ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =9A, dI/dt=100A/μs, V _{DS} =100V	2.8	3.5	4.5	μC

- A. The value of R_{θJA} is measured with the device in a still air environment with T_A=25° C.
- B. The power dissipation P_D is based on T_{J(MAX)}=150° C in a TO252 package, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
- C. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150° C.
- D. The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.
- E. The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.
- F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=150° C.
- G. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C.
- H. L=60mH, I_{AS}=3.8A, V_{DD}=150V, R_G=10Ω, Starting T_J=25° C

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

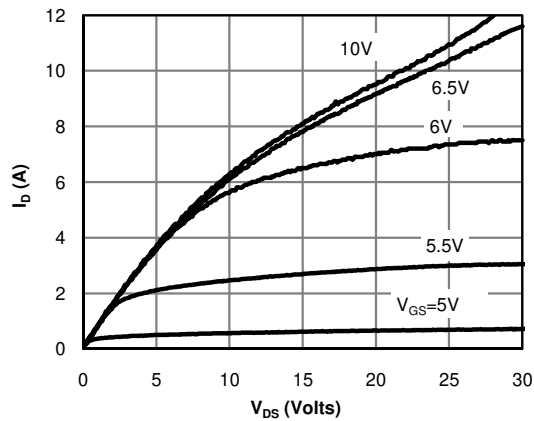


Fig 1: On-Region Characteristics

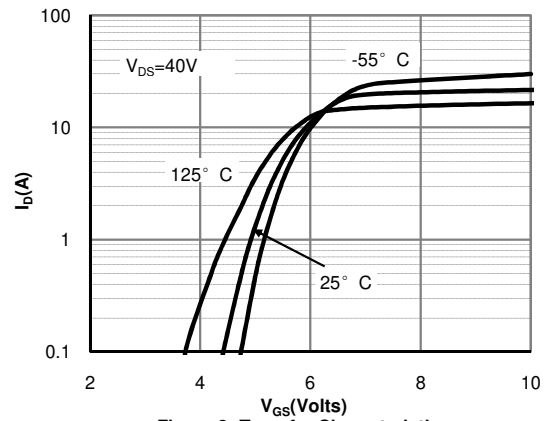


Figure 2: Transfer Characteristics

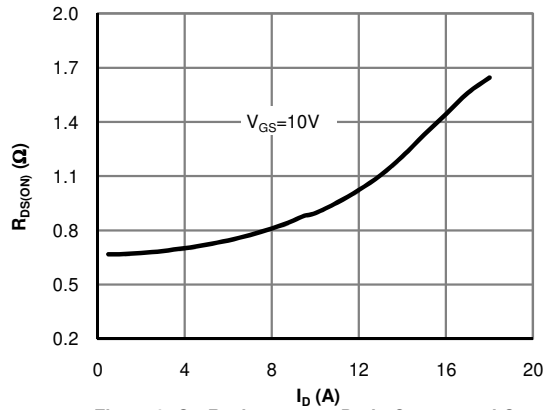


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

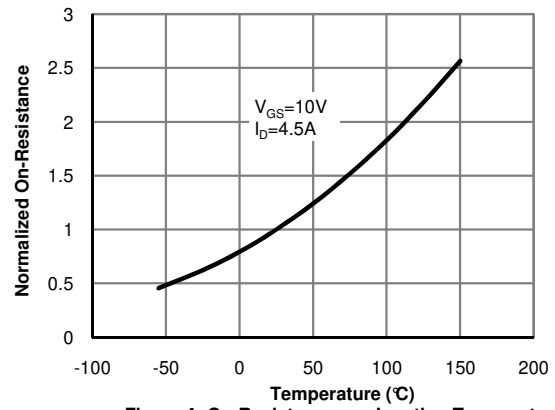


Figure 4: On-Resistance vs. Junction Temperature

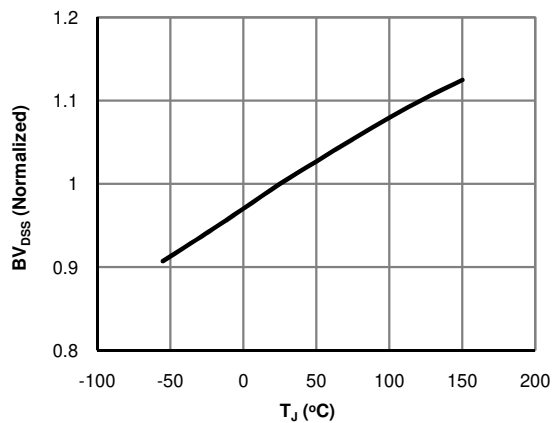


Figure 5: Break Down vs. Junction Temperature

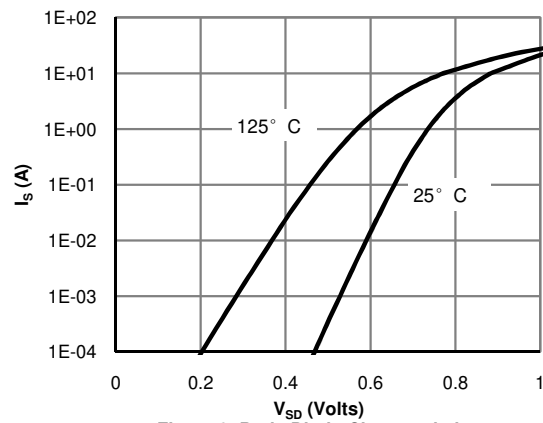


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

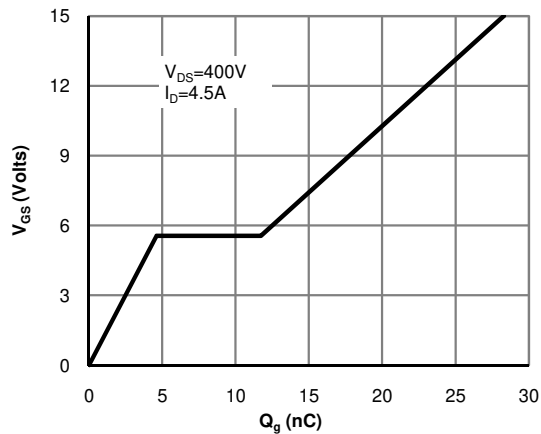


Figure 7: Gate-Charge Characteristics

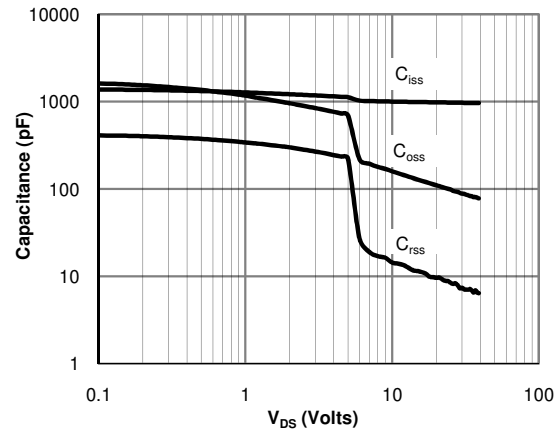


Figure 8: Capacitance Characteristics

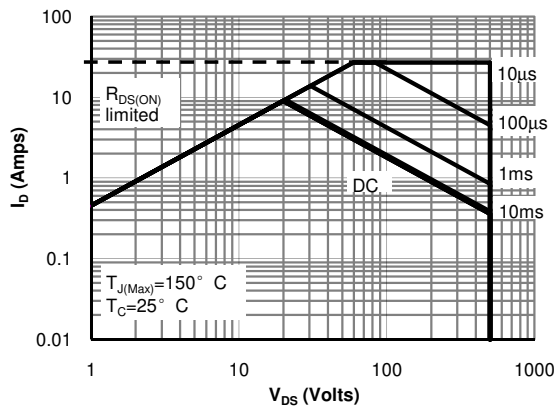


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

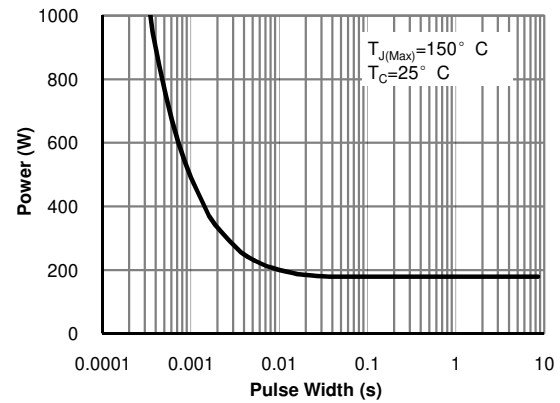


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

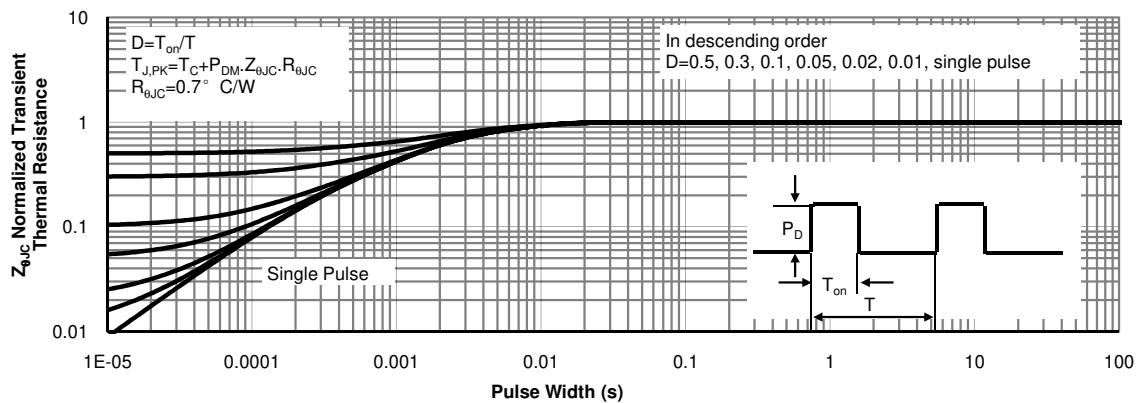


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

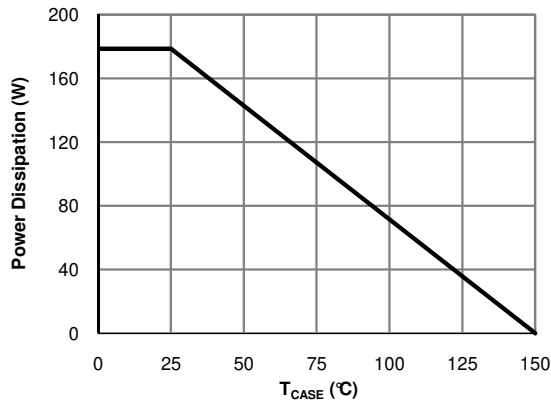


Figure 12: Power De-rating (Note B)

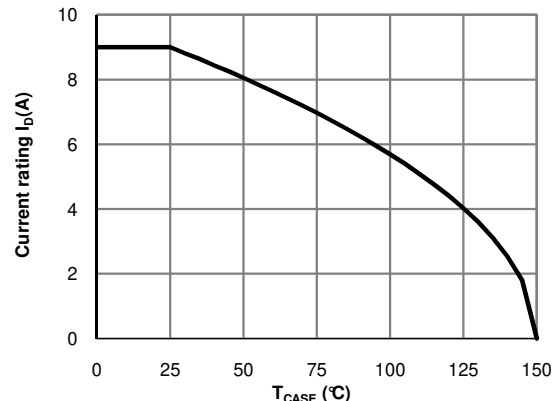


Figure 13: Current De-rating (Note B)

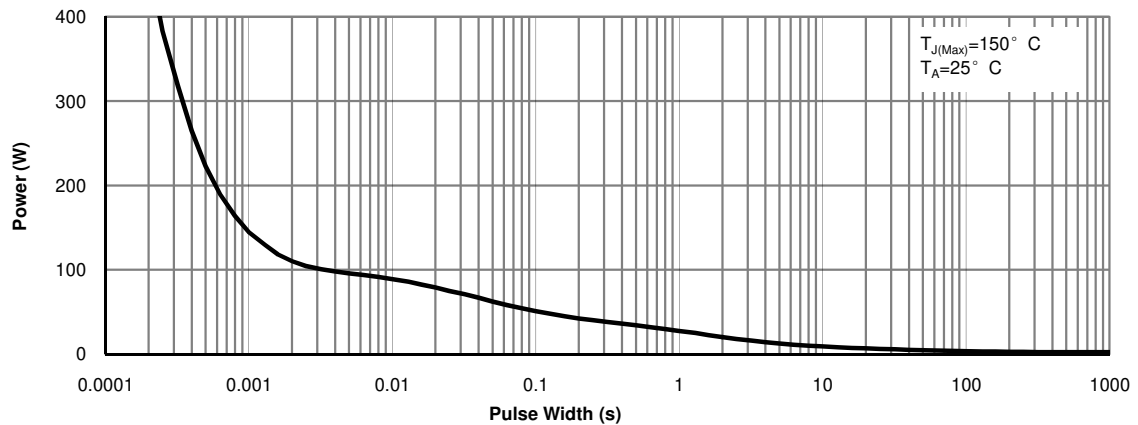


Figure 14: Single Pulse Power Rating Junction-to-Ambient (Note G)

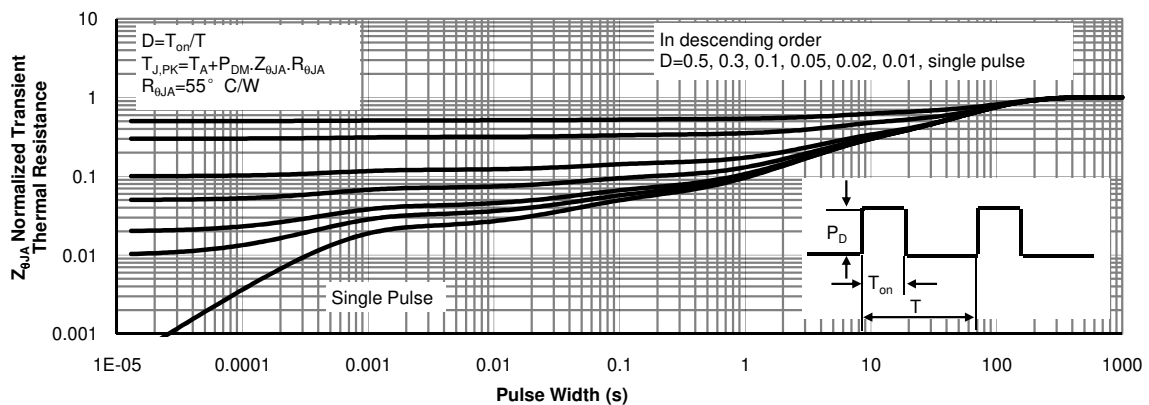
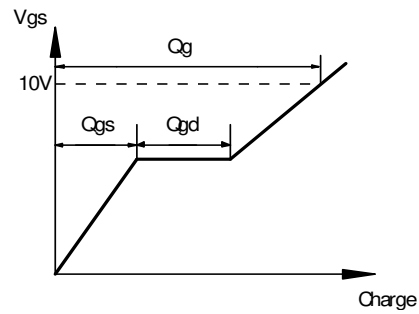
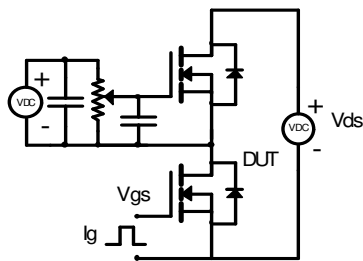
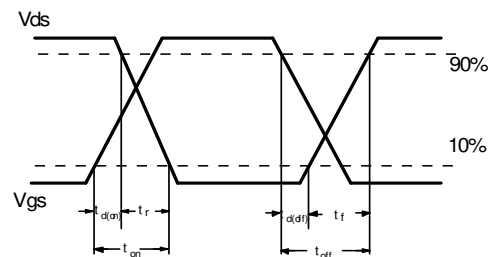
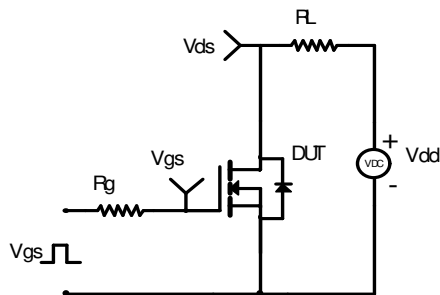


Figure 15: Normalized Maximum Transient Thermal Impedance (Note G)

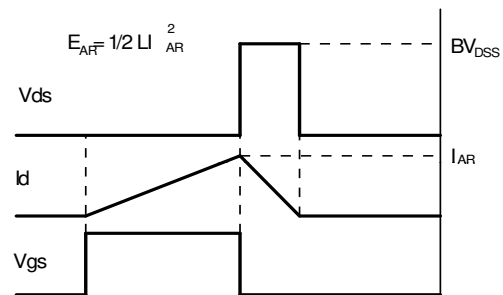
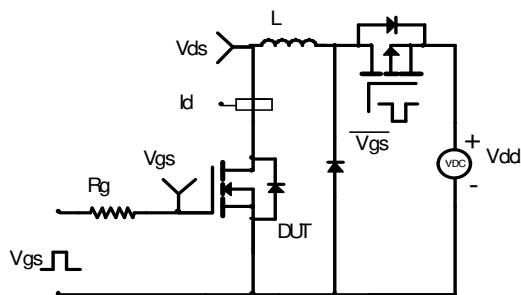
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

